## Supporting Information

**Charge carrier mobility of the organic photovoltaic materials PTB7 and PC71BM and its influence on device performance**

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**[Figure S1](#page-0-0)** shows the hole mobility of  $PTB7:PC_{71}BM$  as a function of temperature. The hole mobility  $(\mu)$  depends almost exponentially on the temperature  $(T)$  as shown by the red fitting line. A simple equation of  $\mu = a \times e^{(T/b)}$  revealed a fit parameter of  $a = 2.75 \times 10^{-9}$  cm<sup>2</sup>/Vs and  $b = 29.2$  K. This relation was used to convert the temperature to the hole mobility



<span id="page-0-0"></span>*Figure S1: Hole mobility of PTB7:PC71BM vs. temperature on a semi-log scale.* 

**[Figure S2](#page-1-0)** shows the open circuit voltage, extracted charge and the integral of the short circuit current for the turn-on behavior of  $PTB7:PC_{71}BM$  solar cells. (This measurement was done on a separate device batch with similar performance.) The extracted charge was measured using a microsecond switch and the method described in the literature [1]. At 77 K the extracted charge reaches saturation at a much longer time scale compared to at room temperature. The steady state value at 77 K is 2.5 times higher than at 295 K.



<span id="page-1-0"></span>*Figure S2: Extracted charge and open circuit voltage vs. illumination time. Increasing light intensity from 0.12 (black) sun to 0.93 sun (magenta)*

[Figure S3](#page-1-1) presents the series resistance of the devices obtained by the slope at high voltage (1.5 V), at the open circuit voltage and from a method based on two JV-curves with different intensity. The method using two JV-curves, which is recommended by the standard for testing solar cells (IEC 60891) [2], agrees well with the slope at  $V_{\text{OC}}$ . All curves show an increase of the series resistance with reducing hole mobility. The series resistance obtained from the two-curve method is approximately proportional to  $\mu^{-1/4}$  (grey line).



<span id="page-1-1"></span>*Figure S3: Series resistance of PTB7:PC71BM solar cells as a function of temperature and hole mobility.* 

The fill factor is strongly influenced by the intensity of illumination as shown in **[Figure S4](#page-2-0)**. At 77 K the fill factor increases from 33 % to 66 % when the light intensity is reduced from 1 sun to 0.01 sun, these values are comparable to the literature [3] . Increased light intensity leads to a higher density of charge carriers and higher bimolecular and trap-assisted recombination rates, giving rise to a decay of the fill factor.



<span id="page-2-0"></span>*Figure S4: Fill factor as a function of light intensity for varying temperature.* 

**[Figure S5](#page-3-0)** shows the collapsed JV-curves of PTB7:PC<sub>71</sub>BM solar cells of varying light intensity from 0.01 sun to 1.01 sun. The curves were normalized at -0.5 V. The spread at short circuit was attributed to trap-assisted recombination and the spread at open circuit to bimolecular recombination [4,5]. Cooling from 325 K to 77 K shows an increase of trapassisted recombination.



<span id="page-3-0"></span>*Figure S5: Collapsed JV-curves normalized at -0.5 V for different temperatures.* 

**[Figure S6](#page-3-1)** shows the fit parameters of the exponent of  $J_{SC}$  vs. intensity and the slope of  $V_{OC}$ vs. intensity. In the region between 200 K and 325 K the mobility has not much influence on the trap-assisted and bimolecular recombination. From 200 K to 77 K bimolecular recombination increases slightly, whereas trap-assisted recombination increases strongly.



<span id="page-3-1"></span>*Figure S6: Fit values of the exponent of JSC vs. intensity and the slope of VOC vs. intensity as a function of temperature and mobility*

## References:

- 1 C.G. Shuttle, A. Maurano, R. Hamilton, B. O'Regan, J.C. de Mello, J.R. Durrant, Charge extraction analysis of charge carrier densities in a polythiophene/fullerene solar cell: Analysis of the origin of the device dark current, Applied Physics Letters. 93 (2008) 183501. doi:10.1063/1.3006316.
- 2 A. Wagner, Peak-power and internal series resistance measurement under natural ambient conditions, in: Proceedings EuroSun, 2000. http://2012.interempresas.net/FeriaVirtual/Catalogos\_y\_documentos/80319/Medidade-Rs-y-Potencia-pico.pdf.
- 3 R. Mauer, I.A. Howard, F. Laquai, Effect of Nongeminate Recombination on Fill Factor in Polythiophene/Methanofullerene Organic Solar Cells, The Journal of Physical Chemistry Letters. 1 (2010) 3500–3505. doi:10.1021/jz101458y.
- 4 S.R. Cowan, A. Roy, A.J. Heeger, Recombination in polymer-fullerene bulk heterojunction solar cells, Physical Review B. 82 (2010). doi:10.1103/PhysRevB.82.245207.
- 5 A.K.K. Kyaw, D.H. Wang, V. Gupta, W.L. Leong, L. Ke, G.C. Bazan, et al., Intensity Dependence of Current–Voltage Characteristics and Recombination in High-Efficiency Solution-Processed Small-Molecule Solar Cells, ACS Nano. 7 (2013) 4569–4577. doi:10.1021/nn401267s.